

# High-speed double diode Rev. 3 — 22 July 2010

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Two high-speed switching diodes fabricated in planar technology, and encapsulated in a small SOT143B Surface-Mounted Device (SMD) plastic package. The diodes are not connected.

#### 1.2 Features and benefits

■ High switching speed:  $t_{rr} \le 4$  ns

Reverse voltage: V<sub>R</sub> ≤ 75 V

Repetitive peak reverse voltage: V<sub>RRM</sub> ≤ 85 V Repetitive peak forward current: I<sub>FRM</sub> ≤ 500 mA

AEC-Q101 qualified Small SMD package

#### 1.3 Applications

High-speed switching in e.g. surface-mounted circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I <sub>F</sub>	forward current		[1] -	-	215	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 75 V	-	-	1	μΑ
$V_R$	reverse voltage		-	-	75	V
t <sub>rr</sub>	reverse recovery time		[2] _	-	4	ns

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB).



<sup>[2]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.

### **High-speed double diode**

### 2. Pinning information

Table 2. Pinning

Table 2.	Finning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode (diode 1)		
2	cathode (diode 2)	4 3	4   3
3	anode (diode 2)		
4	anode (diode 1)	1 2	
			1 2
			006aab100

## 3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BAS28	-	plastic surface-mounted package; 4 leads	SOT143B			

### 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BAS28	JT*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

### **High-speed double diode**

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •	,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
$V_{RRM}$	repetitive peak reverse voltage		-	85	V
$V_R$	reverse voltage		-	75	V
I <sub>F</sub>	forward current		<u>[1]</u> -	215	mA
I <sub>FRM</sub>	repetitive peak forward current		-	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave	<u>[3]</u>		
		t <sub>p</sub> = 1 μs	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		t <sub>p</sub> = 1 s	-	0.5	Α
Per device					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1][2]	250	mW
Tj	junction temperature		-	150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device	; one diode loaded					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W
R <sub>th(j-t)</sub>	thermal resistance from junction to tie-point		-	-	360	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB.

<sup>[2]</sup> One diode loaded.

<sup>[3]</sup>  $T_j = 25$  °C prior to surge.

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### 7. Characteristics

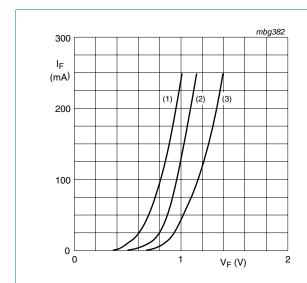
Table 7. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	•					
V <sub>F</sub> forward voltage	forward voltage	I <sub>F</sub> = 1 mA	-	-	715	mV
		I <sub>F</sub> = 10 mA	-	-	855	mV
		$I_F = 50 \text{ mA}$	-	-	1	V
		I <sub>F</sub> = 150 mA	-	-	1.25	V
I <sub>R</sub> revers	reverse current	V <sub>R</sub> = 25 V	-	-	30	nΑ
		V <sub>R</sub> = 75 V	-	-	1	μΑ
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	-	-	30	μΑ
		V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C	-	-	50	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
t <sub>rr</sub>	reverse recovery time		[1] -	-	4	ns
$V_{FR}$	forward recovery voltage		[2] _	-	1.75	V

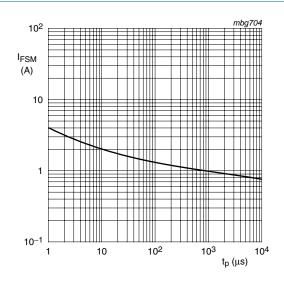
<sup>[1]</sup> When switched from  $I_F = 10$  mA to  $I_R = 10$  mA;  $R_L = 100$   $\Omega$ ; measured at  $I_R = 1$  mA.

<sup>[2]</sup> When switched from  $I_F = 10$  mA;  $t_r = 20$  ns.



- (1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values
- (2)  $T_j = 25$  °C; typical values
- (3)  $T_j = 25 \,^{\circ}C$ ; maximum values

Fig 1. Forward current as a function of forward voltage

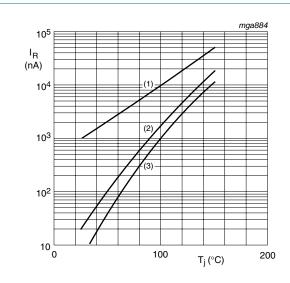


Based on square wave currents.

 $T_j = 25 \,^{\circ}\text{C}$ ; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values

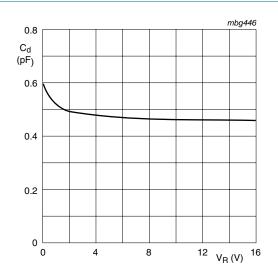
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 $V_R = V_{Rmax}$ 

- (1)  $V_R = 75 \text{ V}$ ; maximum values
- (2)  $V_R = 75 \text{ V}$ ; typical values
- (3)  $V_R = 25 V$ ; typical values

Fig 3. Reverse current as a function of junction temperature



 $f = 1 \text{ MHz}; T_j = 25 ^{\circ}\text{C}$ 

Fig 4. Diode capacitance as a function of reverse voltage; typical values

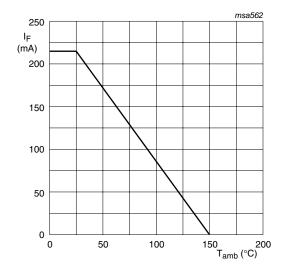
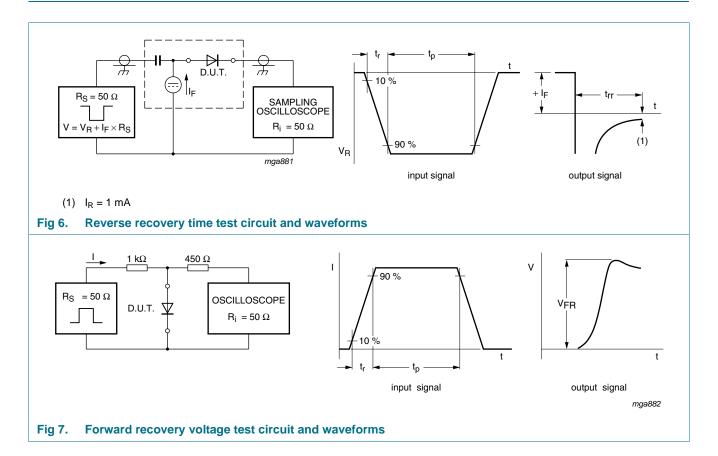


Fig 5. Forward current as a function of ambient temperature; derating curve

**High-speed double diode** 

### 8. Test information

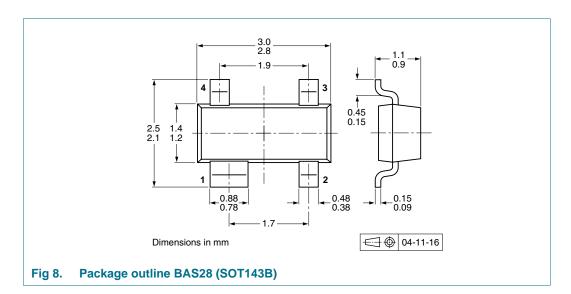


### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 9. Package outline



## 10. Packing information

Table 8. Packing methods

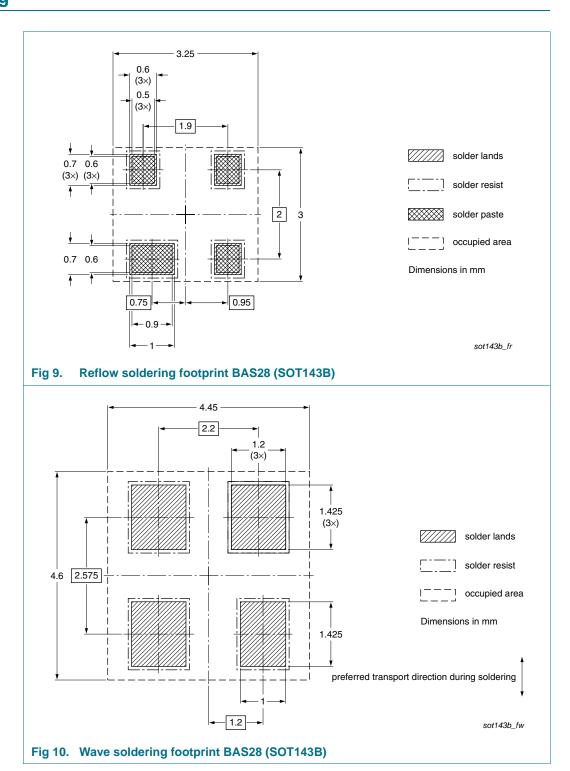
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BAS28	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

### **High-speed double diode**

### 11. Soldering



### High-speed double diode

## 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BAS28 v.3	20100722	Product data sheet	-	BAS28_2			
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity			
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>						
	<ul> <li>Section 1.1</li> </ul>	"General description": ame	ended				
	Section 4 "Marking": updated						
	Table 1 "Quick reference data": added						
	Section 8 "Test information": added						
	Figure 8: superseded by minimized package outline drawing						
	Section 10 "Packing information": added						
	Section 11 "Soldering": added						
	Section 13	"Legal information": update	d				
BAS28_2	19960910	Product specification	-	BAS28_1			
BAS28_1	19960403	Product specification	-	-			

### **High-speed double diode**

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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